(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
6 May 2004 (06.05.2004)

PCT

(10) International Publication Number
WO 2004/038804 A2

(51) International Patent Classification[7]: H01L 29/423, 29/786, 21/336, 29/417

(21) International Application Number: PCT/US2003/032663

(22) International Filing Date: 14 October 2003 (14.10.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/274,867 22 October 2002 (22.10.2002) US

(71) Applicant: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

(72) Inventors: YU, Bin; 1373 Poppy Way, Cupertino, CA 95014 (US). AHMED, Shibly, S.; 350 Elan Village Lane, #105, San Jose, CA 95134 (US). AN, Judy, Xilin; 905 Raintree Court, San Jose, CA 95129 (US). DAKSHINA-MURTHY, Srikanteswara; 10926 Jollyville Road, # 1423, Austin, TX 78759 (US). KRIVOKAPIC, Zoran; 2321 De Varona Place, Santa Clara, CA 95050 (US). WANG, Haihong; 34170 Donahue Terrace, Fremont, CA 94555 (US).

(74) Agent: DANIEL, R., Collopy; Advanced Micro Devices, Inc., One AMD Place, Mail Stop 68, Sunnyvale, CA 94088-3453 (US).

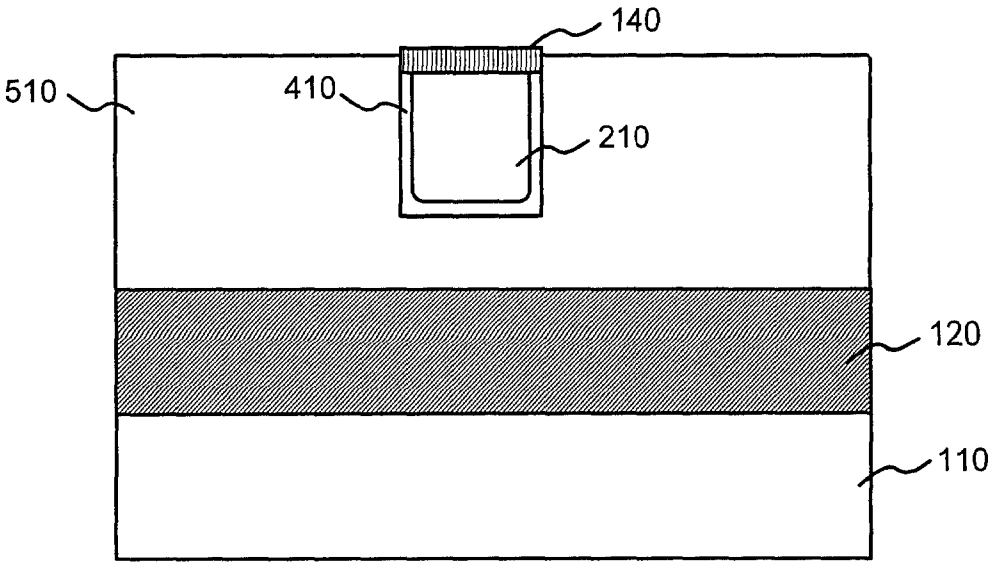
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *without international search report and to be republished upon receipt of that report*

[Continued on next page]

(54) Title: SEMICONDUCTOR DEVICE HAVING A U-SHAPED GATE STRUCTURE



(57) Abstract: A double-gate semiconductor device (100) includes a substrate (110), an insulating layer (120), a fin (210) and agate (510). The insulating layer (120) is formed on the substrate (110) and the gate (510) is formed on the insulating layer (120). The fin (210) has a number of side surfaces, a top surface and a bottom surface. The bottom surface and at least a portion of the side surfaces of the fin (210) are surrounded by the gate (510). The gate material (510) surrounding the fin (210) has a U-shaped cross-section at a channel region of the semiconductor device (100).

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